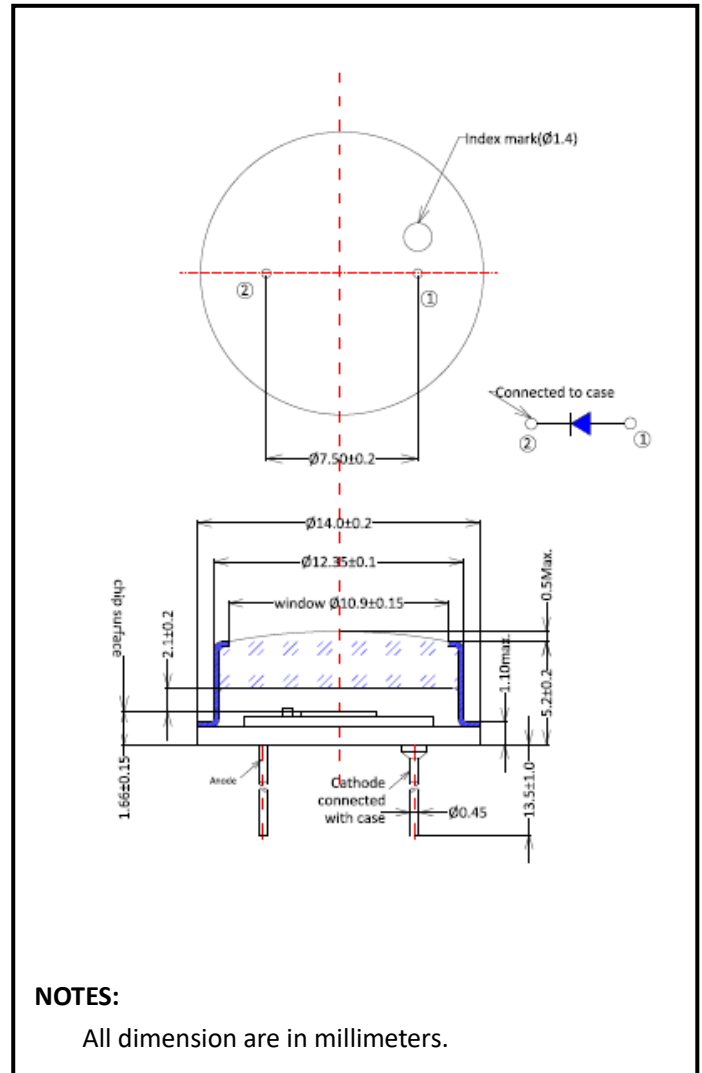
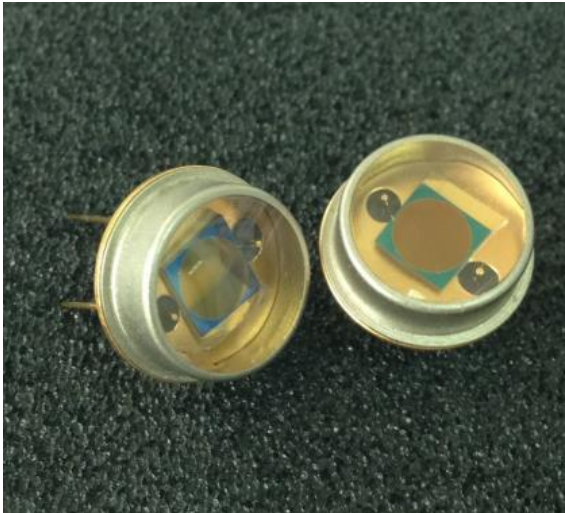


InGaAs PIN Photodiode

IGA5000



Description

OTRON SENSOR IGA5000 is a type of active area size of 5mm diameter active area IR sensitive detectors which exhibit excellent responsivity from 850nm to 1680nm, allowing high sensitivity to weak signals.

These large active area devices are ideal for use in infrared instrumentation and monitoring applications.

We can also custom type according to customer chip size or Package style enquiry.

Features

- * Low voltage operation
- * Isolated type are also available
- * Large Active Area Diameter
- * Spectral Range 850nm to 1700nm

General Ratings

- * Type InGaAs Photodiode
- * High linearity
- * Chip active area: $\phi 5.0$ mm
- * Low dark current

Applications

- * Optical Instrumentation
- * NIR Sensing
- * Laser Power Measurement
- * Power meters

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission.

Specifications are subject change without notice

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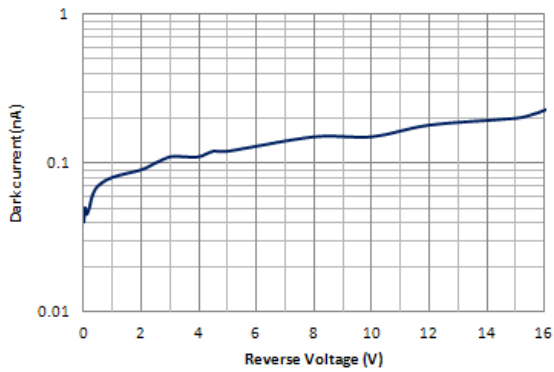


Absolute Maximum Ratings (Ta=25°C)

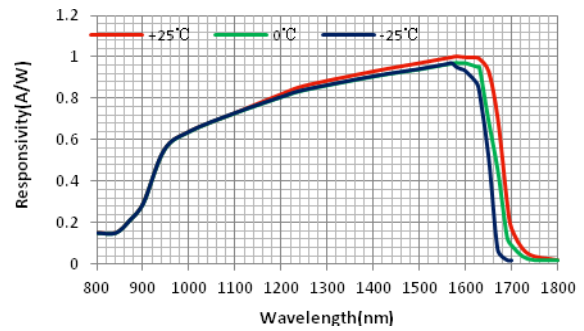
| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|----------------------------|--------------------|--|-----------|----------------------|------|-------------------------|
| Chip size | S | | 5.25*5.25 | | | um |
| Active area | A | | φ5000 | | | um |
| Forward current | I _F | | 10 | | | mA |
| Reverse current | I _R | | 10 | | | mA |
| Dark current | I _D | V _R =0V | | 80 | | pA |
| | | V _R =5V | | 40 | | nA |
| Rise time | t _R | V _R =5V;λ=850nm;R _L =50Ω | | 45 | | ns |
| Forward Voltage | V _F | I _F =1mA | | | 0.5 | V |
| Reverse breakdown voltage | V _{(BR)R} | I _R =10μA Ev=0lx | 35 | 50 | | V |
| Junction Capacitance | C _J | V _R =0V f=1MHz | | 1900 | | pF |
| | | V _R =5V f=1MHz | | 871 | | pF |
| Photo sensitivity | S _R | 1310nm | 0.90 | 0.95 | | A/W |
| | | 1550nm | 0.95 | 1.10 | | |
| Spectral Application Range | λ _{range} | | 850 | | 1680 | nm |
| Spectral Response-Peak | λ _p | | | 1600 | | nm |
| Shunt resistance | R _{sh} | V _R =10mV | | 0.1 | | GΩ |
| Saturation power | L | V _R =0V;λ=1.55μm | | 1 | | mW |
| | | V _R =5V;λ=1.55μm | | 6 | | |
| Angular Resp 50% Resp Pt | θ _{1/2} | | | ±55 | | Degrees |
| Noise Equivalent Power | NEP | V _R =5V λ=1550nm | | 5×10 ⁻¹⁴ | | W/Hz ^{1/2} |
| Specific Detectivity | D* | V _R =5V λ=1550nm | | 8.8×10 ¹² | | cm(Hz/W) ^{1/2} |

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■ Dark current vs. reverse voltage

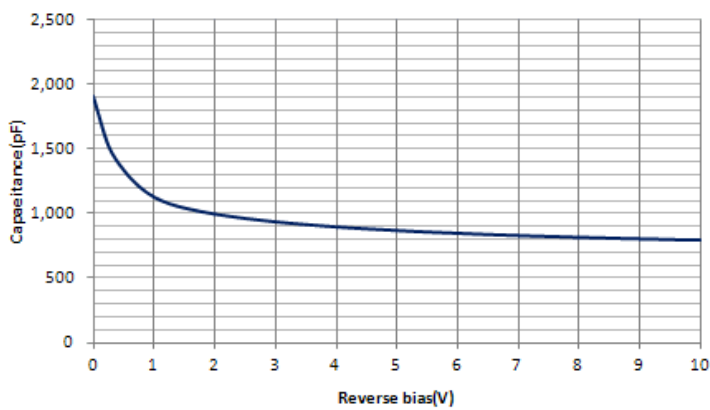


■ Spectral response



■ Relative Junction Capacitance

VS. Voltage



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